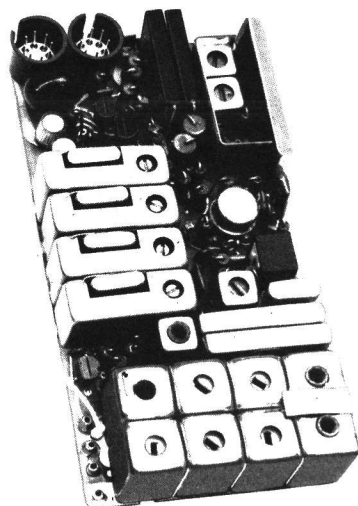


**GE MOBILE RADIO**

**MASTR<sup>®</sup>**

**MVP** *Personal*

**450-470 MHz, RECEIVER TYPE ER-72-A**



**SPECIFICATIONS \***

Audio Output (EIA)	500 milliwatts at less than 5% distortion	
Channel Spacing	25 kHz	
Sensitivity		
12 dB SINAD (EIA Method)	0.35 $\mu$ V	
20 dB Quieting Method	0.50 $\mu$ V	
Selectivity		
EIA Two-Signal	-70 dB at $\pm$ 25 kHz	
20 dB Quieting Method	-110 dB at $\pm$ 25 kHz	
Spurious Response	-60 dB	
Intermodulation (EIA)	-60 dB	
Audio Response	Within +2 and -10 dB of a standard 6 dB per octave de-emphasis curve from 300 to 3000 Hz (1000 Hz reference)	
Modulation Acceptance	$\pm$ 7.5 kHz	
Squelch Sensitivity		
Critical Squelch	0.25 kHz	
Maximum Squelch	Greater than 20 dB Quieting	
Maximum Frequency Spacing	<u>Full Performance</u>	<u>1dB Degradation</u>
	0.60 MHz	1.20 MHz

These specifications are intended primarily for the use of the serviceman. Refer to the appropriate Specification Sheet for the complete specifications.

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## WARNING

No one should be permitted to handle any portion of the equipment that is supplied with high voltage; or to connect any external apparatus to the units while the units are supplied with power. KEEP AWAY FROM LIVE CIRCUITS.

## DESCRIPTION

General Electric MVP Personal Receiver Type ER-72-A, is a one through six-frequency, dual conversion FM receiver for operation in the 450 MHz to 470 MHz range. The receiver is constructed on a single printed wire board and utilizes both discrete components and Integrated Circuit Modules.

References to symbol numbers mentioned in the following text are found on the Schematic Diagram, Outline Diagram and Parts List (see Table of Contents). The typical circuit diagrams used in the text are representative of the circuits used in the Integrated Circuit Modules. A block diagram of the receiver is shown in Figure 1.

Supply voltage for the receiver includes a continuous 7.5 Volts for the squelch module, and a switched 7.5 Volts for the remaining receiver stages.

## CIRCUIT ANALYSIS

### OSCILLATOR MODULE

Oscillator Model 4EG28A28 (450-470 MHz) is a crystal-controlled Colpitts oscillator (see Figure 2). The entire oscillator is contained in a metal can with the receiver operating frequency printed on the top. The crystal frequency ranges from 20.48 to 22.38 MHz, and the crystal frequency is multiplied 21 times.

The oscillator frequency is temperature compensated to provide instant frequency compensation, with a frequency stability of  $\pm 0.0002\%$  from  $0^{\circ}\text{C}$  to  $+55^{\circ}\text{C}$  and  $\pm 0.0005\%$  from  $-30^{\circ}\text{C}$  to  $+60^{\circ}\text{C}$ . The temperature compensation network is contained in Compensator Module A3 on the System Board.

In multi-frequency receivers, additional oscillator modules are mounted on the receiver board. The single-frequency supply jumper is removed, and the proper frequency is selected by connecting the 5.4 Volts to the selected oscillator module through frequency selector switch S1 on the control unit.

Complete instructions for multi-frequency modifications are contained in the Multi-Frequency Modification Diagram (Refer to LBI-4900).

#### NOTE

All oscillator modules are individually compensated at the factory and cannot be repaired in the field. Any attempt to remove the oscillator cover will void the warranty.

### COMPENSATOR

Compensator module A3 contains the temperature compensation network for the oscillator (see Figure 3).

The regulated 5.4 Volts at Pin 2 is applied to a thermistor-compensated voltage divider. The output at Pin 3 (2.35 Volts measured with a VTVM) is applied to Pin 3 and to the varactor in the Oscillator module. At temperatures below  $-10^{\circ}\text{C}$ , the compensated voltages increase to maintain the proper voltage on the oscillator voltage-variable capacitor.

#### SERVICE NOTE

An abnormally low VTVM reading (or no reading) at Pin 3 may indicate a short or leakage path in the oscillator. This can be checked by unsoldering Pin 3, raising it off of the printed board, and taking another reading. If this reading is normal, the problem is in the Oscillator module. If the reading remains low (or zero), the problem is in the Compensator.

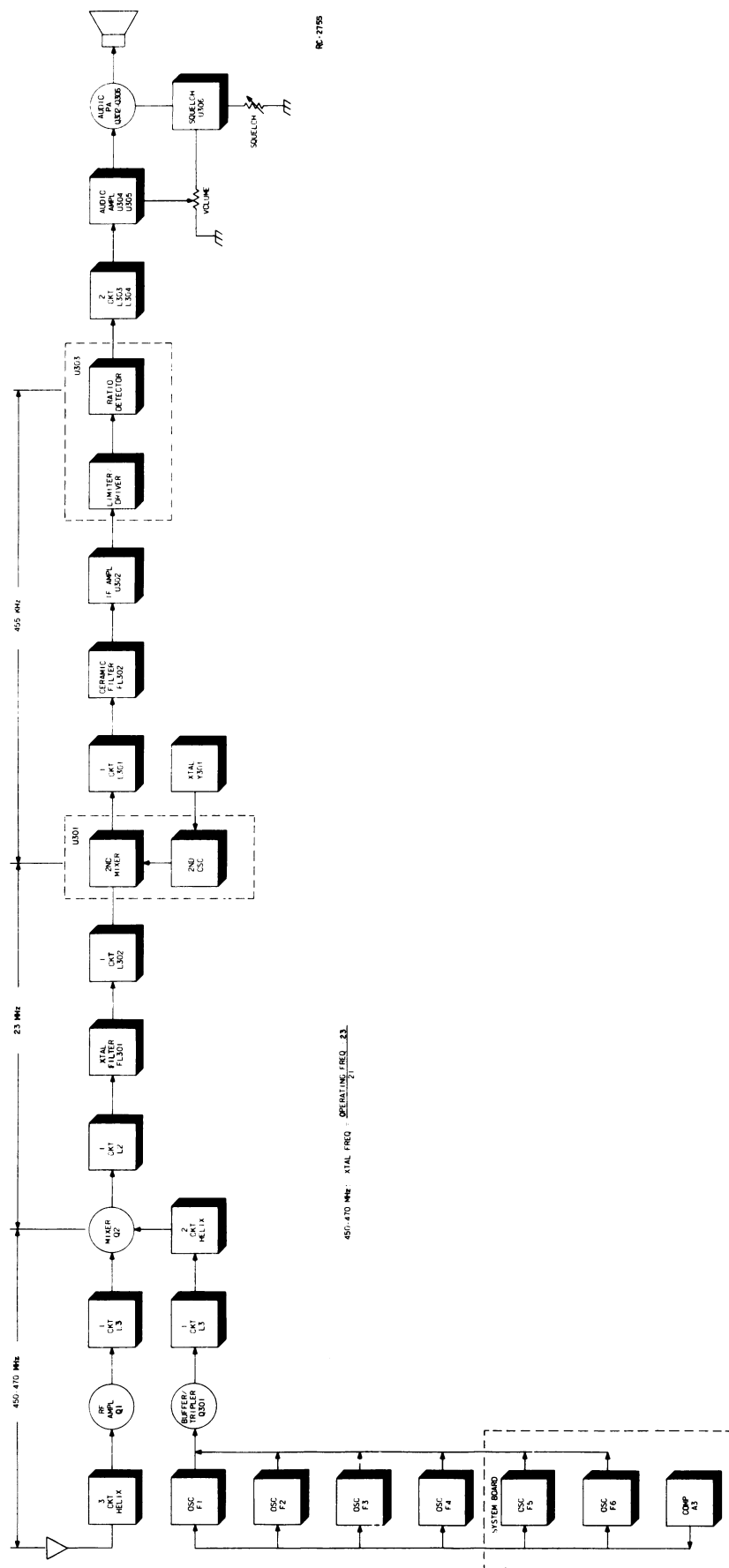
### BUFFER/TRIPLER

RF from the oscillator module is coupled to the base of Buffer/Tripler transistor Q301. Q301 prevents loading of the oscillator modules by the receiver Front End. L3, in the multiplier circuit of the receiver Front End, is part of the collector circuit of Q301 and is tuned to three times the oscillator frequency. Three times the oscillator frequency is metered at Multi-Test Point (TP5) on the receiver board.

### RECEIVER FRONT END

The receiver Front End consists of three tuned helical resonators, an RF amplifier stage, a mixer stage and a multiplier circuit. RF from the antenna is coupled to a tap on L11/L16. The tap is positioned to provide the proper impedance match to the antenna. RF energy is coupled to the third coil (L13/L18) through openings in the sides of the cans. RF is then coupled from a tap on L13/L18 through C8 to the base of RF amplifier transistor Q1. The output of Q1 is developed across tuned circuit C10 and L3, and is applied to the base of the mixer transistor Q2 to be beat against the low-side injection frequency from the Multiplier Circuit.

The output of L3 in the multiplier circuit is applied to the anode of multiplier diode CR1. The two helical resonators following CR1 are tuned to seven times the first multiplier frequency for a total multiplication of 21 times. The output of



**Figure 1 - Receiver Block Diagram**

the helical resonators is direct-coupled to the emitter of the mixer transistor Q2. With the RF signal from the RF amplifier applied to the base of mixer Q2 and the low side injection frequency from the multiplier circuit applied to the emitter, the resultant 23 MHz IF frequency is coupled through the mixer collector tuned circuit (L2 & C6) to Crystal Filter FL301.

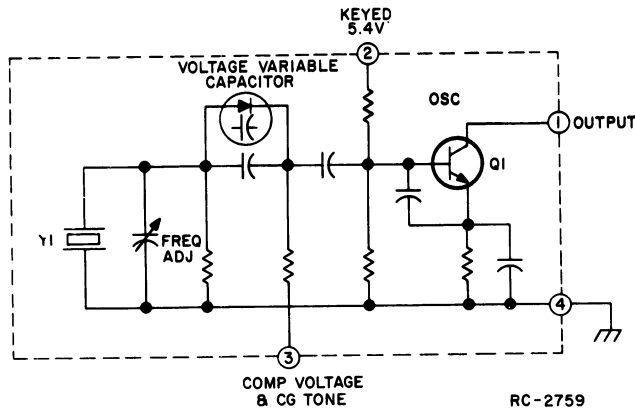


Figure 2 - Typical Oscillator Circuit

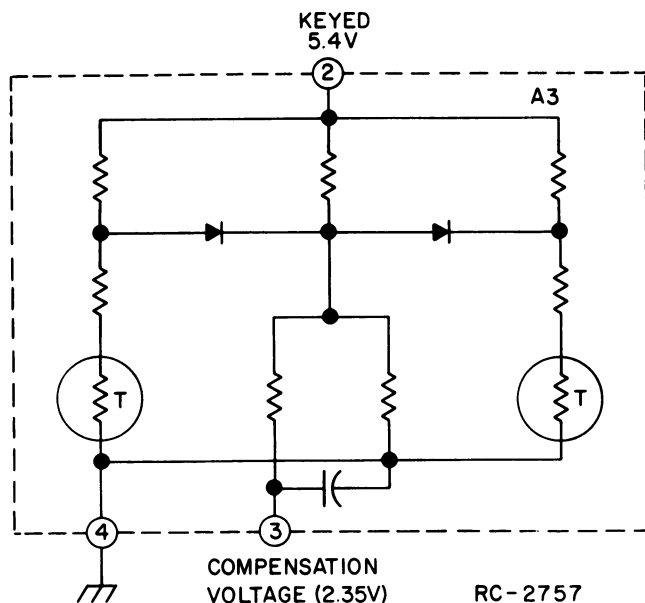


Figure 3 - Typical Compensator Circuit

#### CRYSTAL FILTER

Crystal Filter FL301 follows the receiver Front End mixer stage and provides a minimum of 40 dB stop-band attenuation at

23 MHz. The output of FL301 is coupled through L302 to 2nd Mixer and Oscillator Module U301-1.

#### 2ND MIXER AND OSCILLATOR

The 23 megahertz signal coupled to the 2nd Mixer and Oscillator Module U301-1 is coupled to the base of 2nd Mixer transistor Q2. Also coupled to the base of Q2 is a 22.545 megahertz low side injection frequency from Colpitts oscillator Q1. The 23 megahertz High-IF signal and the 22.545 megahertz low side injection frequency, produce a 455 kilohertz Low-IF output at U301-4. A typical 2nd mixer and oscillator circuit is shown in Figure 4.

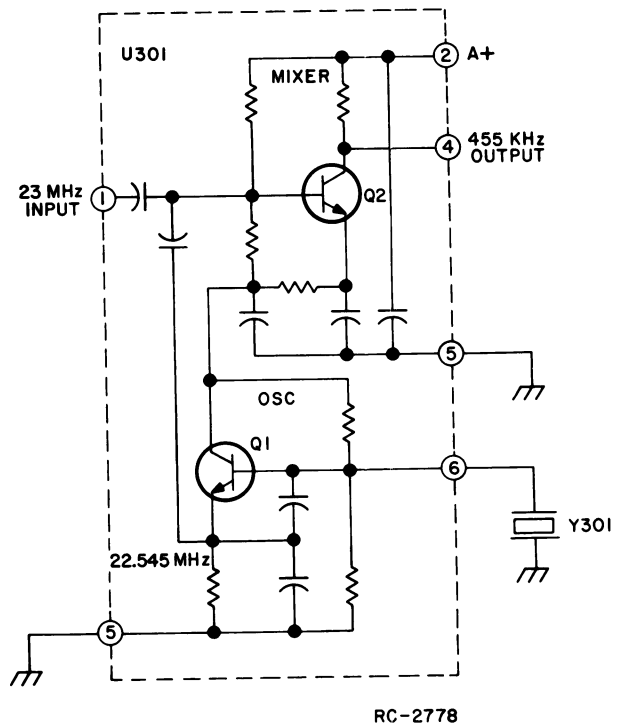
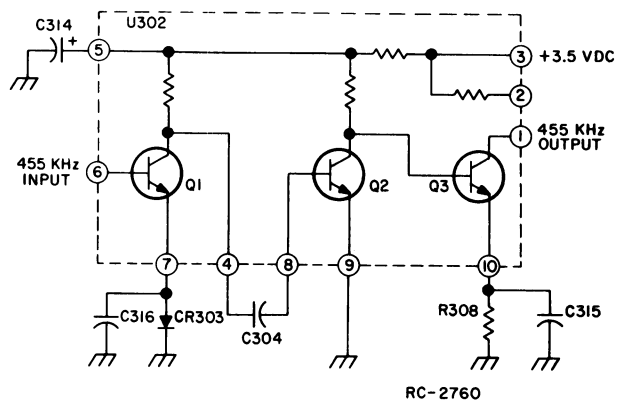


Figure 4 - Typical 2nd Mixer and Oscillator Circuit

The 455 Kiloherertz Low-IF from 2nd Mixer and Oscillator Module U301-4 is coupled through Low-IF Filter L301 and Low-IF Ceramic Filter FL302. L301 and FL302 provide additional selectivity for the receiver. The output from L301 and FL302 is metered at TP4 and coupled to Low-IF Amplifier U302-6.

#### IF AMPLIFIER

The 455 kilohertz Low-IF coupled to IF Amplifier U302-6 is applied to the base of amplifier Q1. A typical IF-amplifier circuit is shown in Figure 5.



**Figure 5 - Typical IF Amplifier Circuit**

Further amplification is obtained through Q2 and Q3. The output of Q3 is applied to U302-1.

## DRIVER/LIMITER AND RATIO DETECTOR

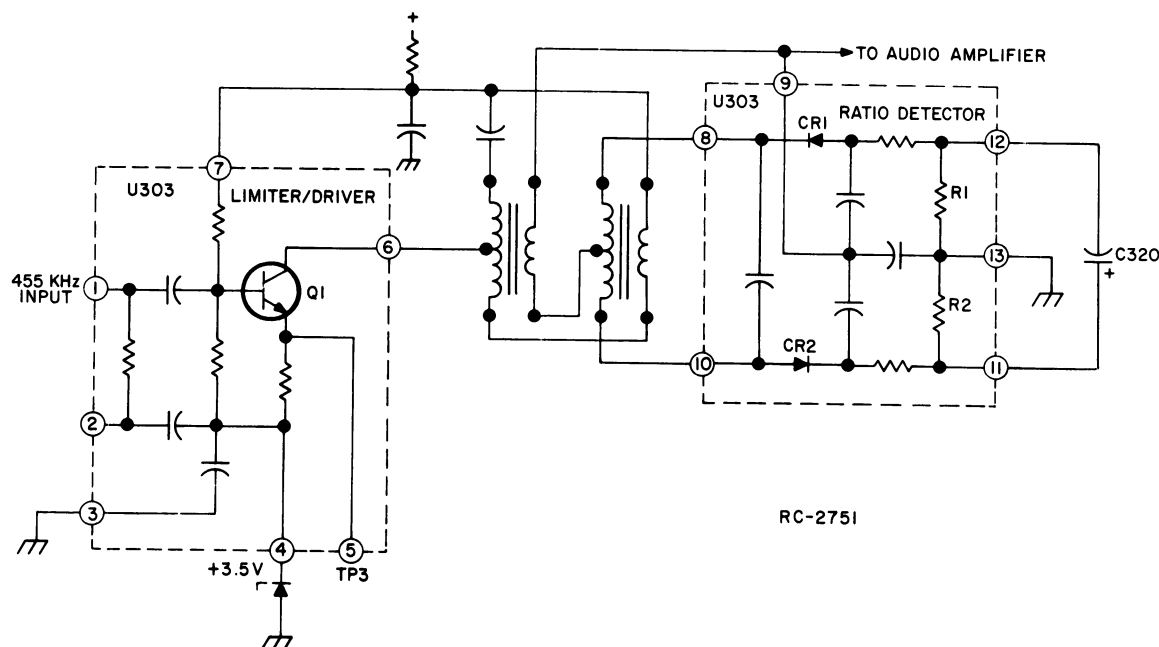
The 455 kilohertz Low-IF from IF Amplifier U302-1 is connected to Driver/Limiter and Ratio Detector Module U303-1. A Typical Driver/Limiter and Ratio Detector Circuit is shown in Figure 6.

The Low-IF is applied to the base of Driver/Limiter transistor Q1. The output of Q1 is connected to U303-6 and applied directly to the Ratio Detector Circuit through L303 and L304. Diodes CR1 and CR2 rectify the Low-If. Voltages, the sum of which always remain constant, develop across resistors R1 and R2. Audio is developed as a result of the varying ratio of the voltages across R1 and R2. C1 stabilizes the circuit and keeps the sum of the voltages across R1 and R2 constant. The recovered audio is coupled from U303-9 through low pass filter R326 and C308. to Audio Amplifier Module U304/U305-1.

## AUDIO AMPLIFIER

Audio and noise from Ratio Detector U303 is applied to Audio Amplifier module U304/U305-1. (U305 in Channel Guard applications). A typical audio amplifier circuit is shown in Figure 7.

Audio and noise is applied to the base of Q1. This stage operates as an emitter-follower for matching the impedance of the ratio detector to amplifier transistor Q2 and VOLUME control R701. The output of Q1 connects from Pin 2 to the base of amplifier Q2 (Pin 4) through the VOLUME control. The output of Q1 is also applied to the input of Squelch module U306.



**Figure 6 - Typical Driver/Limiter and Ratio Detector Circuit**

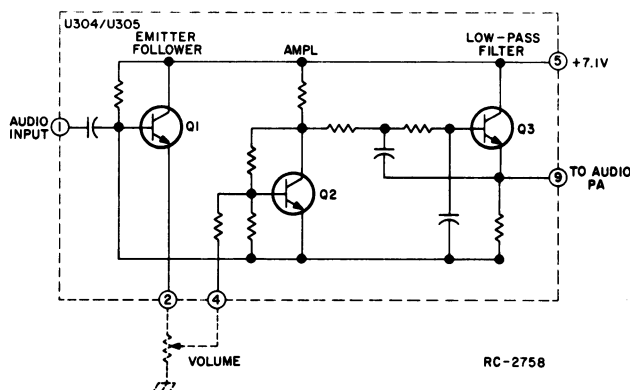


Figure 7 - Typical Audio Amplifier Circuit

Following amplifier Q2 is active low-pass filter Q3. Audio from the filter is connected from Pin 9 to Audio PA transistor Q302. In Audio Amplifier module U310, an active high-pass filter to provide the required tone frequency roll-off.

#### AUDIO PA

When the receiver is quieted by a signal, audio from the active filter, in Audio Amplifier Module U304/U305, is coupled to the base of amplifier transistor Q302. The output of Q302 is direct coupled to the base of Driver transistor Q303. Q303 supplies drive for PA transistors Q304 and Q306. Q304 is driven direct from the collector of Q303. Drive from the collector of Q303 is applied to the base of bootstrap transistor Q305. The emitter of Q305 is direct coupled to Q306.

PA transistors Q304 and Q306 operate as complementary emitter-followers, providing a 500 milliwatt output into an 8-ohm load. Audio is coupled through capacitor C329 on the receiver board to speaker LS1.

#### SQUELCH

Noise from Audio Amplifier U304/U305 operates the squelch circuit. A typical squelch circuit is shown in Figure 8.

When no carrier is present in the receiver, the noise output of active high-pass filter Q1 is coupled to the base of noise amplifier Q2 through SQUELCH control R702. R702 controls the gain of the noise amplifier.

The output of noise amplifier Q2 is detected by diodes CR1 and CR2, and the resultant positive voltage turns off the PNP squelch switch Q3. In standard radios, the emitter of Q3 is connected to +7 Volts by means of a jumper from H1 to H2. When noise turns off Q3, its collector drops to ground potential. As the collector of Q3 is connected to the base of amplifier Q301 in the Audio PA module, turning off Q3 also turns off Q301, keeping the audio PA turned off.

When the receiver is quieted by a signal, squelch switch Q3 turns on. This applies +7 Volts to the base of amplifier Q1 in the Audio PA module, turning the Audio PA circuit on so that sound is heard at the speaker.

In tone decoder applications, the 7-Volt jumper from H1 to H2 is removed. The emitter of squelch switch Q3 is connected to 7.5 Volts by a DC switch on the decoder board.

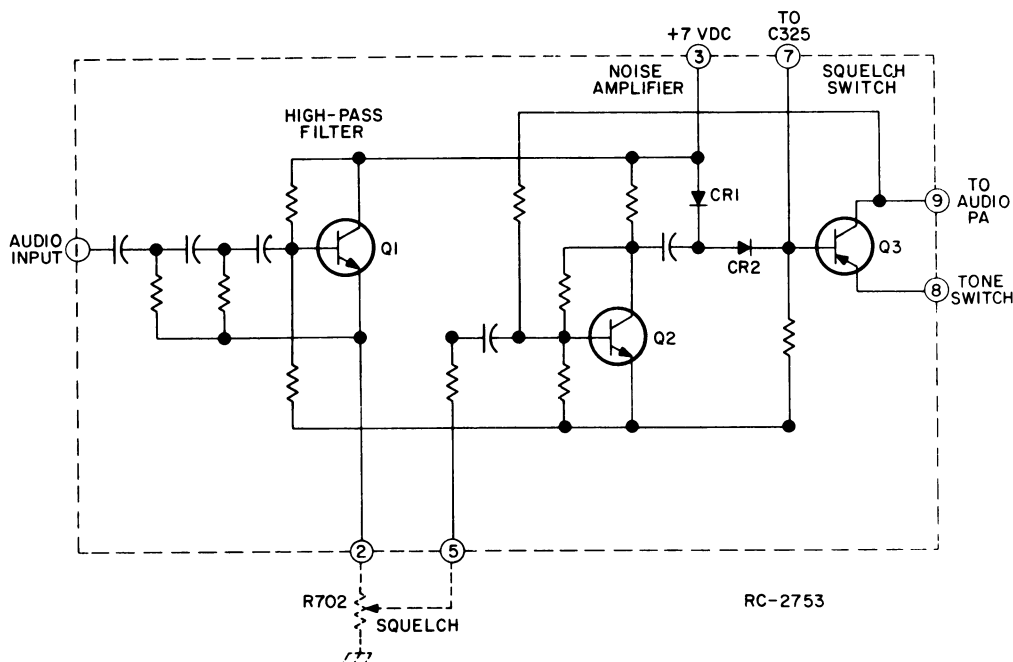


Figure 8 - Typical Squelch Circuit





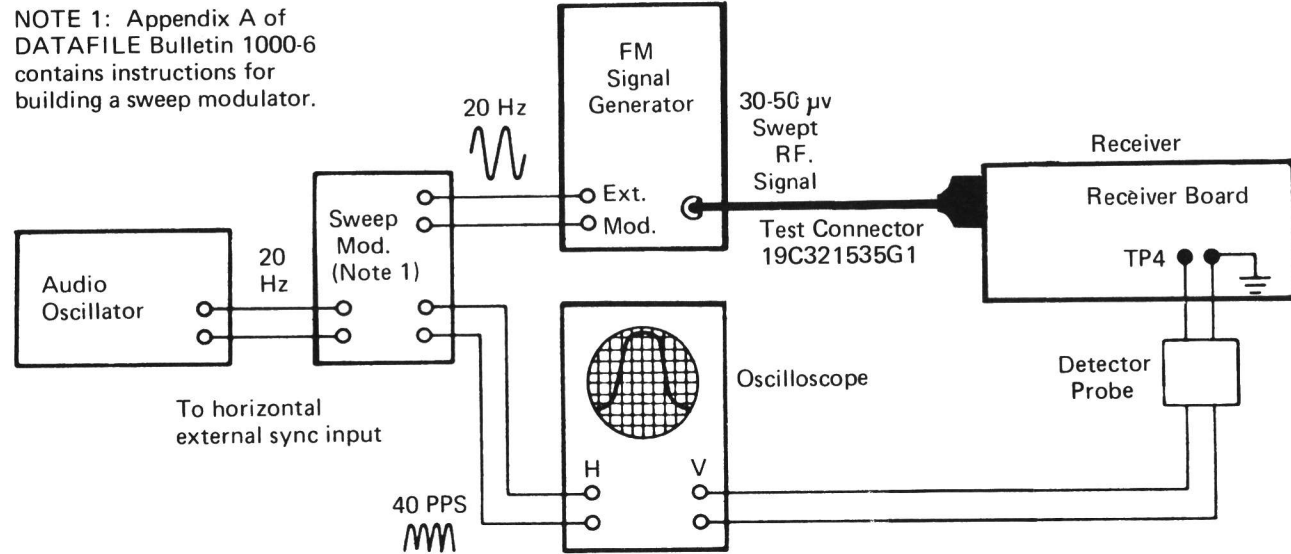


Figure 9 - Test Setup for 20-Hz Double-Trace Sweep Alignment

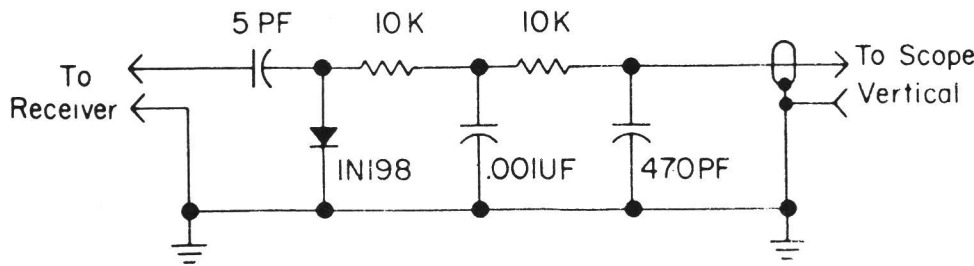
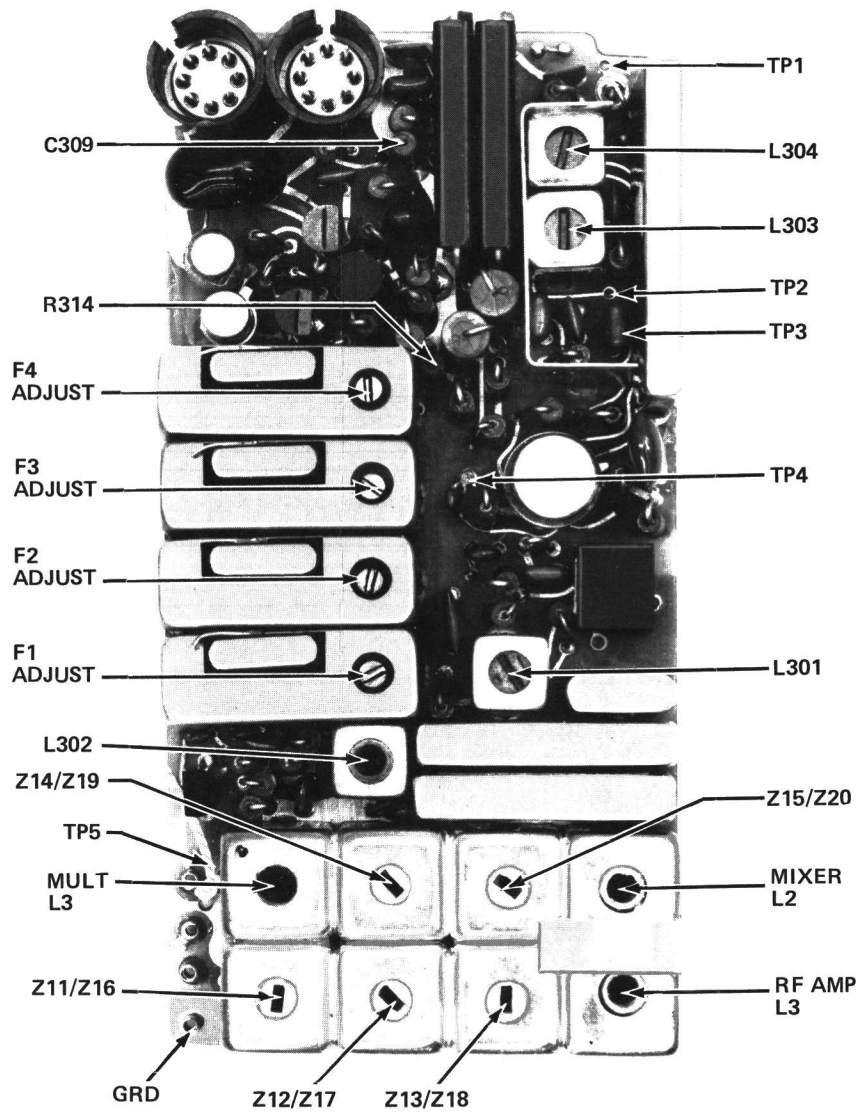


Figure 10 - Detector Probe for Sweep Alignment



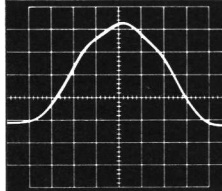
EQUIPMENT

1. A 23 MHz signal source (GE IF Generator Model 4EX9A10 or equivalent), a 455 kHz signal source (GE IF Generator Model 4EX7A10 or equivalent), and a 450-470 MHz source connected to the receiver through Receiver Test Connector 19C321535G1 inserted into antenna tube 19A127779G8.
2. GE Test Set Model 4EX3A10 or 4EX8K11 or voltmeter with equivalent sensitivity.
3. GE Test Amplifier Model 4EX16A10 and RF probe 19C311370G1, or equivalent RF voltmeter.
4. Distortion Analyzer or AC-VTVM.
5. Oscilloscope, 50 MV/DIV or better.

PRELIMINARY CHECKS AND ADJUSTMENTS

1. In multi-frequency receivers where the maximum frequency spacing is less than one MHz, align the receiver on the F1 channel. Where the frequency spacing is more than one MHz, align the receiver on the center frequency.
2. Set the slugs in Z11/Z16 thru Z15/Z20 to the bottom of the coil form for frequencies in the low end of the band. Set the slugs near the top of the coil form for frequencies near the high end of the band.
3. Set the slug in RF AMP L3 to the top of the coil form for frequencies in the low end of the band, and near the bottom of the coil form for frequencies near the high end of the band. Set Mixer Output coil L2 near the middle of the coil form.
4. Connect the negative lead of the DC Test Set to TP1 and the positive lead to ground. Connect the Distortion Analyzer or AC-VTVM across the speaker leads.

ALIGNMENT PROCEDURE

STEP	TUNING CONTROL	PROCEDURE
RATIO DETECTOR		
1.	L303	Lightly couple a 455 kHz signal to U302-6. Adjust input for a slight increase at U303-12 (TP1) Tune L303 for a peak.
2.	L304	Adjust L304 to zero volts $\pm 10$ mV at TP2. Repeat steps 1 and 2. Disconnect 455 kHz generator.
FRONT END MULTIPLIER		
3	MULT L3	Adjust L3 for maximum meter reading at TP5.
4.	Z14/Z19 and Z15/Z20	Adjust Z14/Z19 and then Z15/Z20 for slight change in meter reading at TP5.
HIGH AND LOW IF		
The IF Circuits have been aligned at the factory and will normally require no further adjustment. Should alignment become necessary, use the procedure outlined in Steps 5 and 6.		
5.	See Procedure	Connect the scope, signal generator and detector as shown in Figures 9 and 10. Apply an on-frequency signal using the lowest possible input level to avoid limiting. Modulate the generator with 20 Hz at 10 to 16 kHz deviation. <div>NOTE An on-frequency signal is easily determined by zero beating the channel signal with the 455 kHz marker generator signal. Loosely couple the 455 kHz generator to U301-4 and adjust the RF level of the RF signal generator to 20 dB quieting level</div>
6.	L2, L302, L301	Tune L2 of the mixer and L302 for the best response. Tune L301 for flatness. Retune L2, L302 and L301 for the best shape on scope as shown on scope wave form, keeping the signal below saturation. <div></div>
FRONT END		
7.	Z11/Z16 thru Z13/Z18 and RF. Amp L3	Apply an on-frequency signal and adjust Z11/Z16, Z12/Z17, Z13/Z18, and L3 for best quieting sensitivity.
8.	MULT L3, Z14/Z19 & Z15/Z20	De-tune L3. Increase the on-frequency input signal and tune Z14/Z19 and Z15/Z20 for best quieting sensitivity. Now re-adjust L3 for maximum meter reading at TP5.
9.	L303, L304	Re-tune the ratio detector on noise. Peak L303 at TP1. Zero TP2 by tuning L304. Detector idling should be zero volts $\pm 10$ mV.
FREQUENCY ADJUSTMENT		
10.		While applying an on-frequency signal, loosely couple a 455 kHz signal to the receiver. Adjust the oscillator trimmers for zero beat frequency between the two signals.  Alternate Method: With no signal, measure and record the output of the ratio-detector with a DC-VTVM at TP2. Apply a strong on-frequency signal and tune the oscillator trimmers for the meter reading obtained at TP2.

ALIGNMENT PROCEDURE

450—470 MHz MVP PERSONAL RECEIVER  
TYPE ER-72-A

## TEST PROCEDURES

These Test Procedures are designed to help you to service a receiver that is operating --- but not properly. The problems encountered could be low power, poor sensitivity, distortion, and low gain. By following the sequence of test steps starting with Step 1, the defect can be quickly localized.

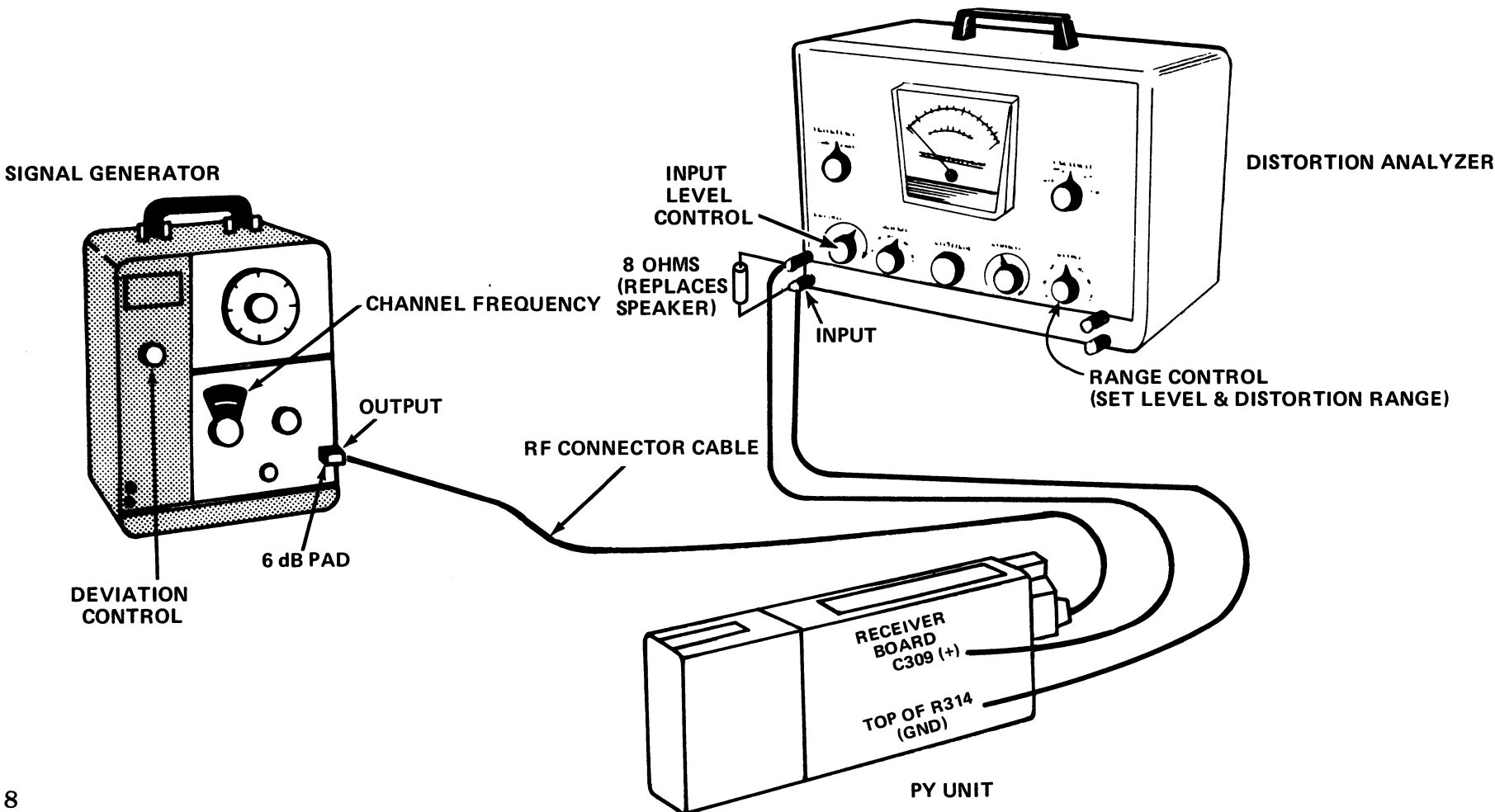
Once the defective stage is pin-pointed, refer to the "Service Check" listed to correct the problem. Additional corrective measures are included in the Troubleshooting Procedure. Before starting with the Receiver Test Procedures, be sure the receiver is tuned and aligned to the proper operating frequency.

### TEST EQUIPMENT REQUIRED

- Distortion Analyzer similar to: Heath IM-12
- Signal Generator similar to: Measurements M-803
- 6-dB attenuation pad
- 8 ohm, 1 watt resistor
- RF Connector Cable 19C321535G1

### PRELIMINARY ADJUSTMENTS

1. Connect the test equipment to the receiver as shown for all steps of the receiver Test Procedure. Refer to page 7 for connection points.
2. Turn the SQUELCH control fully clockwise for all steps of the Test Procedure.
3. Turn on all of the equipment and let it warm up for 20 minutes.



### STEP 1

#### AUDIO POWER OUTPUT AND DISTORTION TEST PROCEDURE

Measure Audio Power output as follows:

- A. Connect a 1,000-microvolt test signal modulated by 1,000 hertz  $\pm 3.0$  kHz deviation to the Antenna Connector.
- B. Set the Volume Control for a 500 milli-watt output (2 volts RMS).
- C. Make distortion measurements according to manufacturer's instructions. Reading should be less than 5%-10% (5% is typical). If the receiver sensitivity is to be measured, leave all controls and equipment as they are.

#### SERVICE CHECK

If the distortion is more than 5%, or maximum audio output is less than 0.5 watt, make the following checks:

- D. Battery voltage---low voltage will cause distortion. (Refer to Receiver Schematic Diagram for voltages.)
- E. Audio Gain (Refer to Receiver Troubleshooting Procedure).

### STEP 2

#### USABLE SENSITIVITY (12 dB SINAD)

##### TEST PROCEDURE

If STEP 1 checks out properly, measure the receiver sensitivity as follows:

- A. Apply a 1000-microvolt, on-frequency signal modulated by 1000 Hz with 3.0 kHz deviation to the Antenna Connector.
- B. Place the RANGE switch on the Distortion Analyzer in the 200 to 2000-Hz distortion range position (1000-Hz filter in the circuit). Tune the filter for minimum reading or null on the lowest possible scale (100%, 30%, etc.)
- C. Place the RANGE switch to the SET LEVEL position (filter out of the circuit) and adjust the input LEVEL control for a +2 dB reading on a mid range (30%).
- D. While reducing the signal generator output, switch the RANGE control from SET LEVEL to the distortion range until a 12-dB difference (+2 dB to -10 dB) is obtained between the SET LEVEL and distortion range positions (filter out and filter in).

- E. The 12-dB difference (Signal plus Noise and Distortion to noise plus distortion ratio) is the "usable" sensitivity level. The sensitivity should be less than rated 12 dB SINAD specification with an audio output of at least 250 milliwatts.
- F. Leave all controls as they are and all equipment connected if the Modulation Acceptance Bandwidth test is to be performed.

#### SERVICE CHECK

If the sensitivity level is more than rated 12 dB SINAD, check the alignment of the RF stages as directed in the Alignment Procedure, and make the gain measurements as shown on the Troubleshooting Procedure.

### STEP 3

#### MODULATION ACCEPTANCE BANDWIDTH (IF BANDWIDTH)

##### TEST PROCEDURE

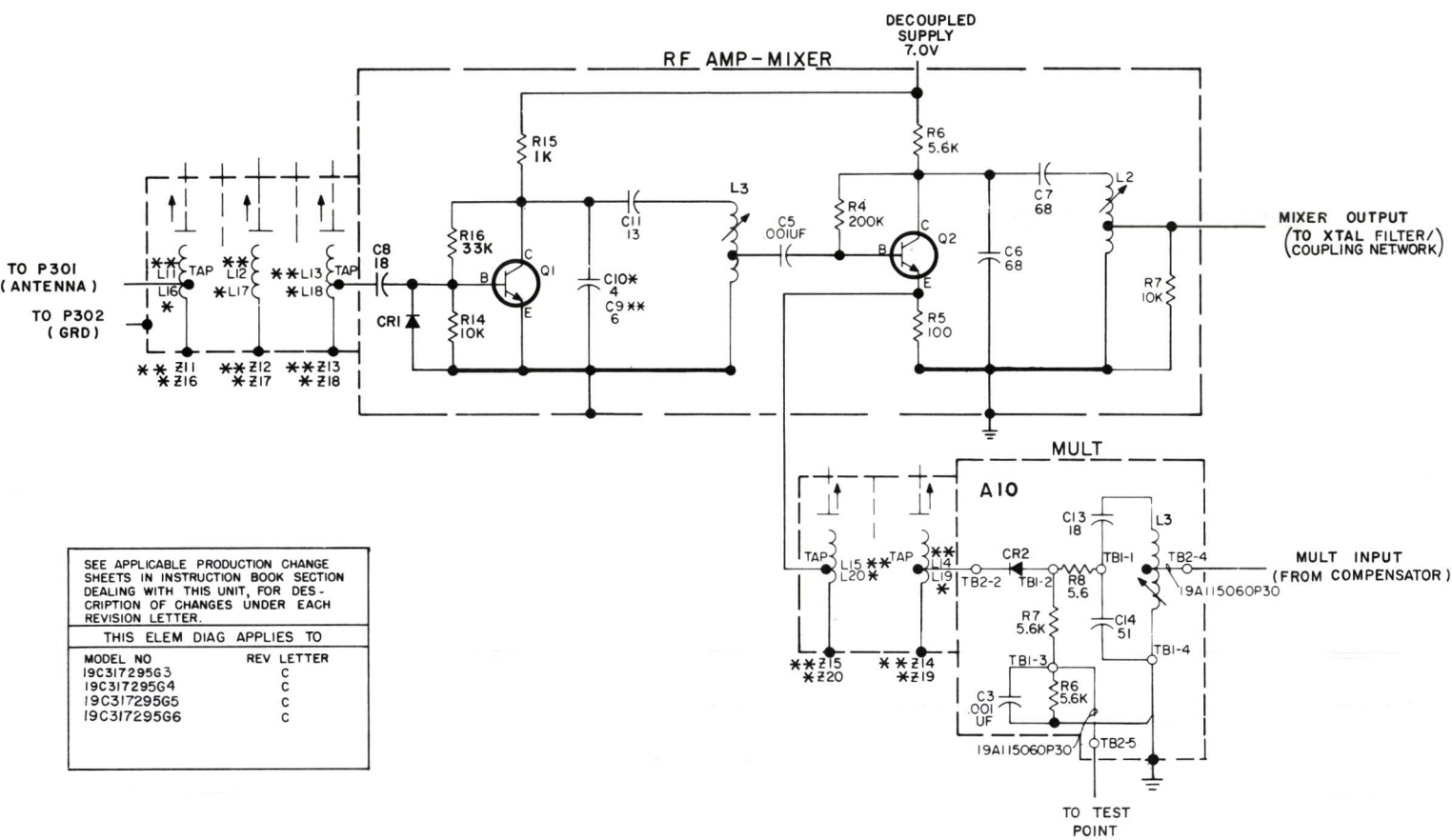
If STEPS 1 and 2 check out properly measure the bandwidth as follows:

- A. Set the Signal Generator output for twice the microvolt reading obtained in the 12-dB SINAD measurement.
- B. Set the RANGE control on the Distortion Analyzer in the SET LEVEL position (1000-Hz filter out of the circuit), and adjust the input LEVEL control for a +2 dB reading on the 30% range.
- C. While increasing the deviation of the Signal Generator, switch the RANGE control from SET LEVEL to distortion range until a 12-dB difference is obtained between the SET LEVEL and distortion range readings (from +2 dB to -10 dB).
- D. The deviation control reading for the 12-dB difference is the Modulation Acceptance Bandwidth of the receiver. It should be more than  $\pm 7$  kHz (but less than  $\pm 9$  kHz).

#### SERVICE CHECK

If the Modulation Acceptance Bandwidth test does not indicate the proper width, make gain measurements as shown on the Receiver Troubleshooting Procedure.

SCHEMATIC DIAGRAM



SEE APPLICABLE PRODUCTION CHANGE SHEETS IN INSTRUCTION BOOK SECTION DEALING WITH THIS UNIT, FOR DESCRIPTION OF CHANGES UNDER EACH REVISION LETTER.

THIS ELEM DIAG APPLIES TO	
MODEL NO	REV LETTER
19C31729563	C
19C31729564	C
19C31729565	C
19C31729566	C

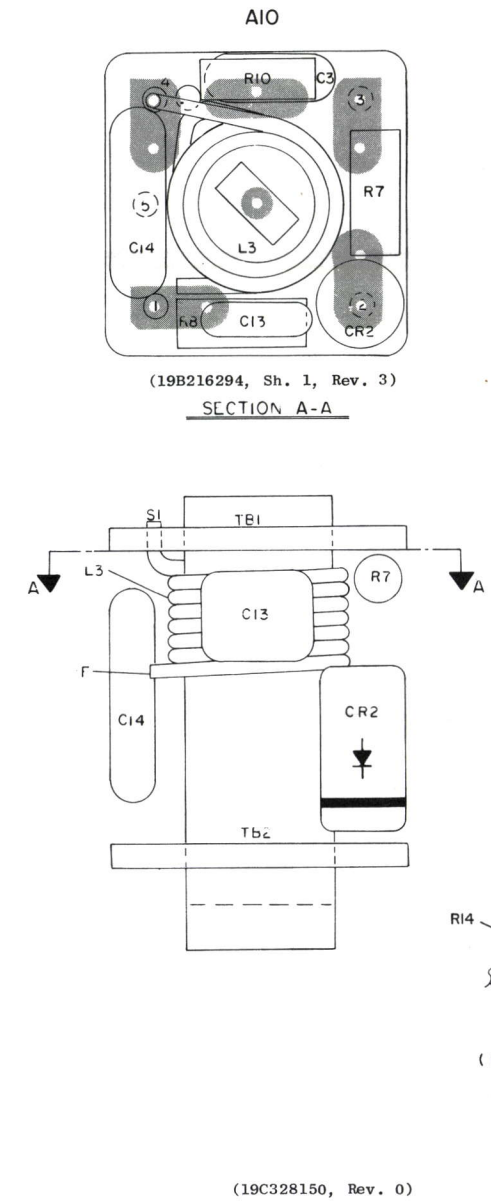
ALL RESISTORS ARE 1/8 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K=1000 OHMS OR MEG=1,000,000 OHMS. CAPACITOR VALUES IN PICOFARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF= MICROFARADS. INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H=HENRYS.

IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART

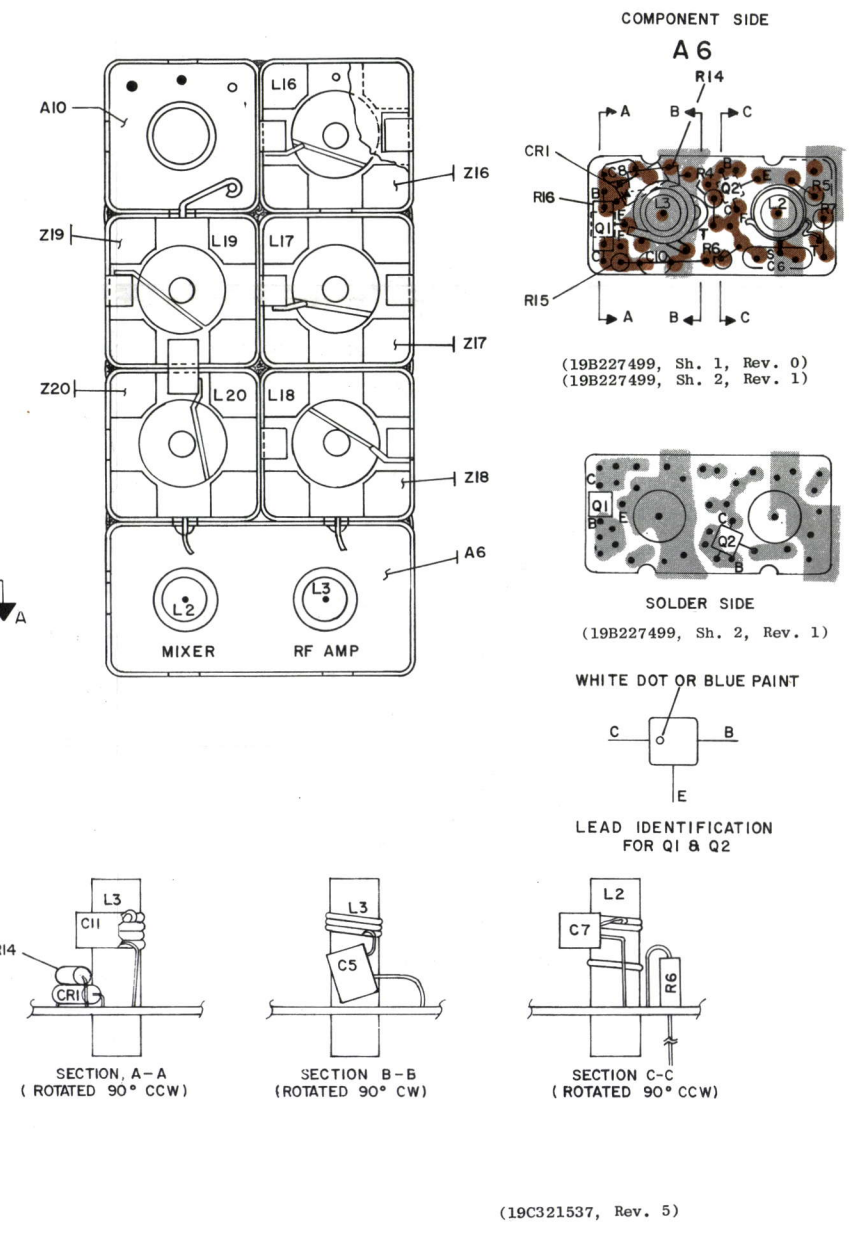
\* HI SPLIT (450-470)  
\*\* LO SPLIT (406-420)

(19C320887, Rev. 7)

OUTLINE DIAGRAM



(19C328150, Rev. 0)



OUTLINE & SCHEMATIC DIAGRAM

450-470 MHz RECEIVER FRONT END (A307)  
TYPE ER-72-A

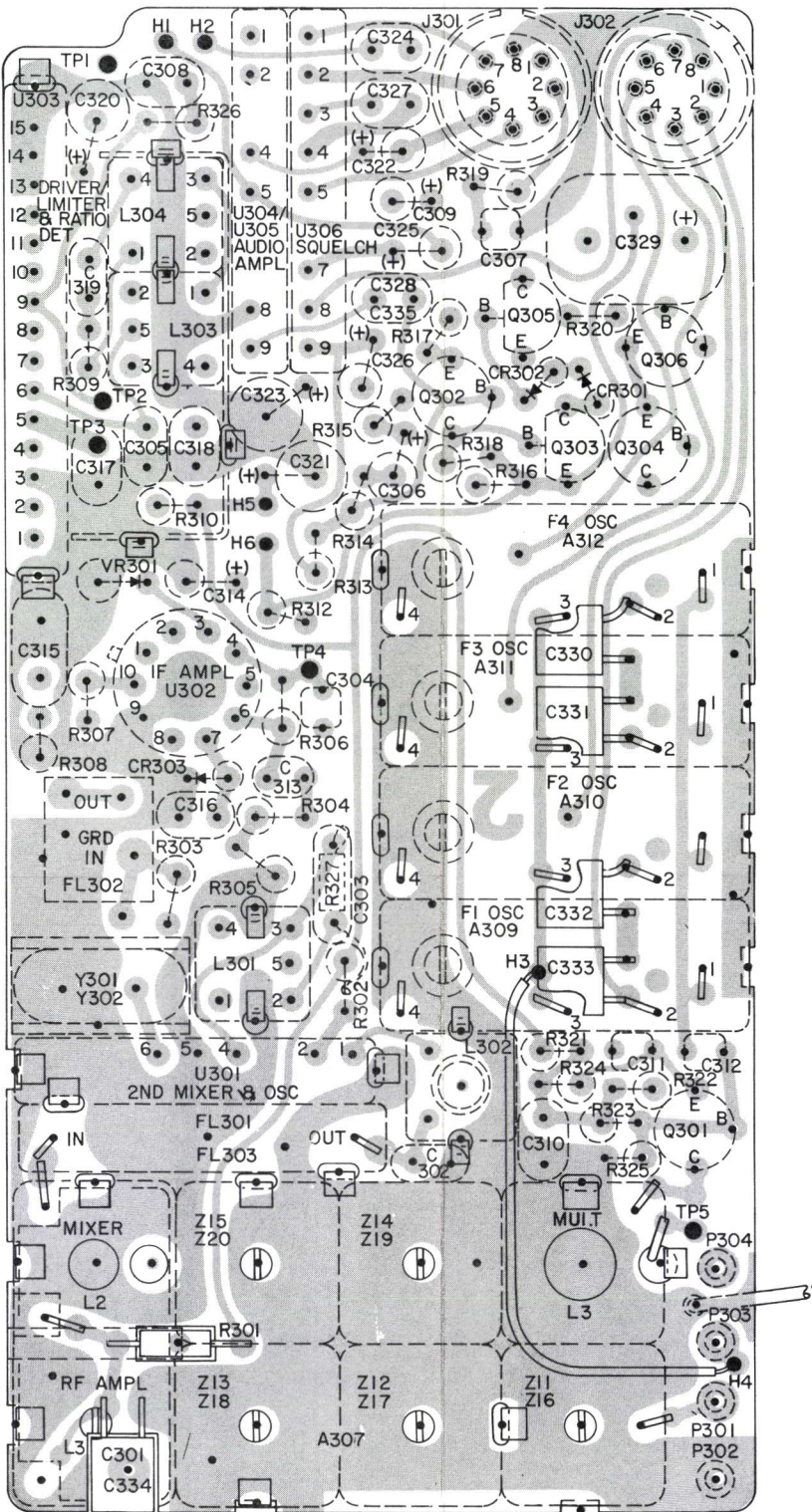


COMPONENT SIDE



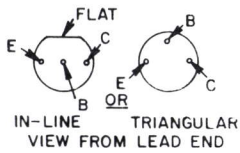
(19D423092, Sh. 2, Rev. 2)  
(19D423092, Sh. 3, Rev. 1)

SOLDER SIDE



(19D423092, Sh. 2, Rev. 2)

LEAD IDENTIFICATION  
FOR Q301-Q306

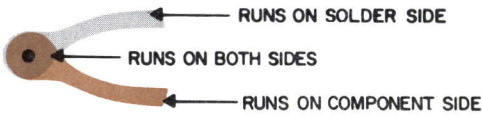


NOTE: LEAD ARRANGEMENT, AND NOT  
CASE SHAPE, IS DETERMINING  
FACTOR FOR LEAD IDENTIFICATION

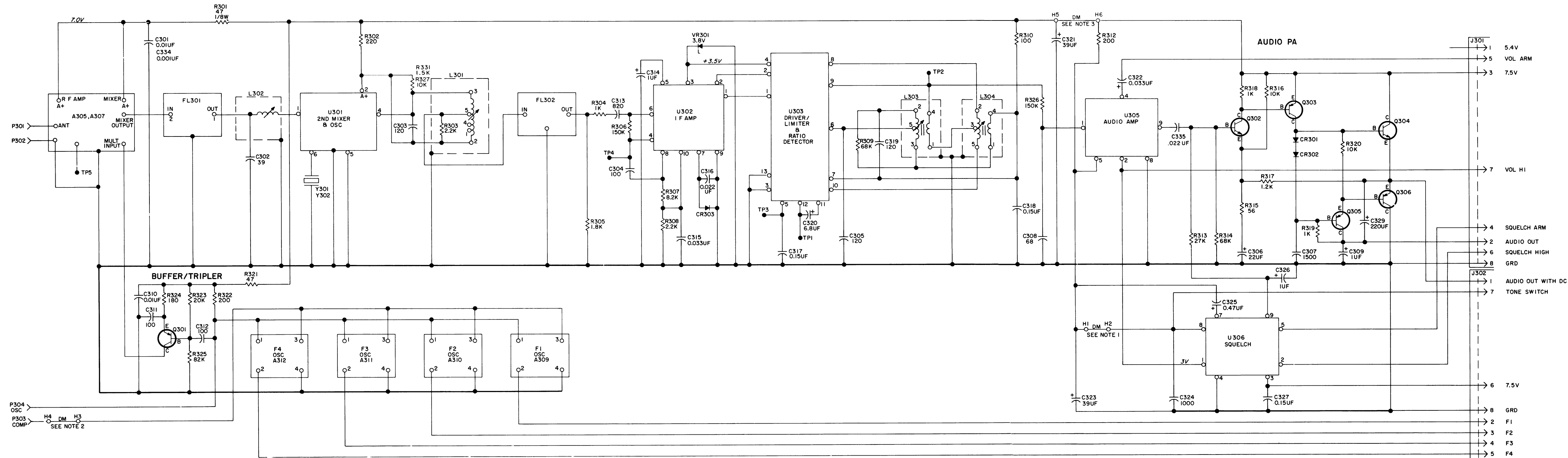
OUTLINE DIAGRAM

450—470 MHz MVP PERSONAL RECEIVER  
TYPE ER-72-A

(19D423382, Rev. 4)







ALL RESISTORS ARE 1/4 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K=1000 OHMS OR MEG=1,000,000 OHMS. CAPACITOR VALUES IN PICO FARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF= MICROFARADS. INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H= HENRYS

IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.

- NOTES:
1. JUMPER PRESENT IN G1 AND G3 ONLY.
  2. JUMPER PRESENT IN G3 AND G4 ONLY.
  3. JUMPER PRESENT IN ALL GROUPS

SEE APPLICABLE PRODUCTION CHANGE SHEETS IN INSTRUCTION BOOK SECTION DEALING WITH THIS UNIT, FOR DESCRIPTION OF CHANGES UNDER EACH REVISION LETTER.	
THIS ELEM DIAG APPLIES TO	
MODEL NO.	REV LETTER
PL19D423091 G1	E
PL19D423091 G2	E
PL19D423091 G3	D
PL19D423091 G4	D

SCHEMATIC DIAGRAM

450—470 MHz MVP PERSONAL RECEIVER  
TYPE ER-72-A

PARTS LIST		
LBI4891E		
450-470 MHZ RECEIVER ER-72-A		
SYMBOL	GE PART NO.	DESCRIPTION
A307		FRONT END ASSEMBLY 19C317295G6
A6*		RF AMPLIFIER 19C317445G4 (Added by REV C)
C5	5495323P12	Ceramic: .001 $\mu$ f +100% -20%, 75 VDCW.
C6 and C7	19A116114P4059	Ceramic: 68 pf $\pm$ 5%, 100 VDCW; temp coef -220 PPM.
C8	19A116114P6038	Ceramic: 18 pf $\pm$ 5%, 100 VDCW; temp coef -470 PPM.
C10	19A116114P2014	Ceramic: 4 pf $\pm$ 5%, 100 VDCW; temp coef -80 PPM.
C11	19A116114P2035	Ceramic: 13 pf $\pm$ 5%, 100 VDCW; temp coef -80 PPM.
CR1	19A116052P1	Diodes and Rectifiers - Silicon.
L2	19B216948G1	Coil.
L3	19A128005G1 19B209436P1	Coil. Includes: Tuning slug.
Q1 and Q2	19A116159P1	Transistors - Silicon, NPN.
R4	3R151P204J	Resistors - Composition: 200K ohms $\pm$ 5%, 1/8 w.
R5	3R151P101J	Composition: 100 ohms $\pm$ 5%, 1/8 w.
R6	3R151P562J	Composition: 5.6K ohms $\pm$ 5%, 1/8 w.
R7	3R151P103J	Composition: 10K ohms $\pm$ 5%, 1/8 w.
R14	3R151P103J	Composition: 10K ohms $\pm$ 5%, 1/8 w.
R15	3R151P102J	Composition: 1K ohms $\pm$ 5%, 1/8 w.
R16	3R151P333J	Composition: 33K ohms $\pm$ 5%, 1/8 w.
A6*		RF AMPLIFIER 19C317445G4 (Deleted by REV C)
C5	5495323P12	Ceramic: .001 $\mu$ f +100% -20%, 75 VDCW.
C6 and C7	19A116114P4059	Ceramic: 68 pf $\pm$ 5%, 100 VDCW; temp coef -220 PPM.
C8	19A116114P6038	Ceramic: 18 pf $\pm$ 5%, 100 VDCW; temp coef -470 PPM.
C10	19A116114P2014	Ceramic: 4 pf $\pm$ 5%, 100 VDCW; temp coef -80 PPM.
C11	9A116114P2035	Ceramic: 13 pf $\pm$ 5%, 100 VDCW; temp coef -80 PPM.
CR1	19A116052P1	Diodes and Rectifiers - Silicon.
L2	19B216948G1	Coil.
L3	19A128005G1 19B209436P1	Coil. Includes: Tuning slug.
Q1 and Q2	19A116159P1	Transistors - Silicon, NPN.
R4	3R151P204J	Resistors - Composition: 200K ohms $\pm$ 5%, 1/8 w.
R5	3R151P101J	Composition: 100 ohms $\pm$ 5%, 1/8 w.
R6	3R151P562J	Composition: 5.6K ohms $\pm$ 5%, 1/8 w.
R7	3R151P103J	Composition: 10K ohms $\pm$ 5%, 1/8 w.
R14	3R151P103J	Composition: 10K ohms $\pm$ 5%, 1/8 w.
R15	3R151P102J	Composition: 1K ohms $\pm$ 5%, 1/8 w.
R16	3R151P333J	Composition: 33K ohms $\pm$ 5%, 1/8 w.
A6*		RF AMPLIFIER 19C317445G4 (Deleted by REV C)
C5	5495323P12	Ceramic: .001 $\mu$ f +100% -20%, 75 VDCW.
C6 and C7	19A116114P4059	Ceramic: 68 pf $\pm$ 5%, 100 VDCW; temp coef -220 PPM.
C8	19A116114P6038	Ceramic: 18 pf $\pm$ 5%, 100 VDCW; temp coef -470 PPM.
C10	19A116114P2014	Ceramic: 4 pf $\pm$ 5%, 100 VDCW; temp coef -80 PPM.
C11	9A116114P2035	Ceramic: 13 pf $\pm$ 5%, 100 VDCW; temp coef -80 PPM.
CR1	19A116052P1	Diodes and Rectifiers - Silicon.
L2	19B216948G1	Coil.
L3	19A128005G1 19B209436P1	Coil. Includes: Tuning slug.

SYMBOL	GE PART NO.	DESCRIPTION
Q1 and Q2	19A116159P1	Transistors - Silicon, NPN.
R4	3R151P204J	Resistors - Composition: 200K ohms $\pm$ 5%, 1/8 w.
R5	3R151P101J	Composition: 100 ohms $\pm$ 5%, 1/8 w.
R6	3R151P562J	Composition: 5.6K ohms $\pm$ 5%, 1/8 w.
R7	3R151P103J	Composition: 10K ohms $\pm$ 5%, 1/8 w.
R14	3R151P103J	Composition: 10K ohms $\pm$ 5%, 1/8 w.
R15	3R151P102J	Composition: 1K ohms $\pm$ 5%, 1/8 w.
R16	3R151P333J	Composition: 33K ohms $\pm$ 5%, 1/8 w.
A10		Multiplier 19C311873G7
C3	5495323P12	Ceramic: .001 $\mu$ f +100% -20%, 75 VDCW.
C13	19A116114P2038	Ceramic: 18 pf $\pm$ 5%, 100 VDCW; temp coef -80 PPM.
C14	19A116114P2054	Ceramic: 51 pf $\pm$ 5%, 100 VDCW; temp coef -80 PPM.
CR2	19A116809P1	Diodes and Rectifiers - Silicon.
L3	19B216296P3 19B200495P5	Coil. Includes: Tuning slug.
R7	3R151P562J	Composition: 5.6K ohms $\pm$ 5%, 1/8 w.
R8	3R151P5R6J	Composition: 5.6 ohms $\pm$ 5%, 1/8 w.
R10	3R151P562J	Composition: 5.6K ohms $\pm$ 5%, 1/8 w.
L16	19B216439G7 19C311750P1	Helical resonator. (Part of Z16). Includes: Tuning slug.
L17	19B216439G2 19C311750P1	Helical resonator. (Part of Z17). Includes: Tuning slug.
L18	19B216439G1 19C311750P1	Helical resonator. (Part of Z18). Includes: Tuning slug.
L19	19B216439G4 19C311750P1	Helical resonator. (Part of Z19). Includes: Tuning slug.
L20	19B216439G3 19C311750P1	Helical resonator. (Part of Z20). Includes: Tuning slug.
Z16		Helical Resonators - Consists of L16 and 19D413132P24 can.
Z17		Consists of L17 and 19D413132P3 can.
Z18		Consists of L18 and 19D413132P25 can.
Z19		Consists of L19 and 19D413132P19 can.
Z20		Consists of L20 and 19D413132P20 can.
A309 thru A312	4EG28A28	Receiver Board 19D423091G3 STANDARD 19D423091G4 CHANNEL GUARD  NOTE: When reordering, give GE Part Number and specify exact frequency needed.  Oscillator Module. 450-470 MHz. $F_x = \frac{F_0 - 23}{21}$

SYMBOL	GE PART NO.	DESCRIPTION
C302	19A116114P2050	Capacitors - Ceramic: 39 pf $\pm$ 5%, 100 VDCW; temp coef -80 PPM.
C303	19A116114P5068	Ceramic: 120 pf $\pm$ 5%, 100 VDCW; temp coef -330 PPM.
C304	19A116114P13064	Ceramic: 100 pf $\pm$ 10%, 100 VDCW; temp coef -5600 PPM.
C305	19A116288P9	Ceramic: 120 pf $\pm$ 5%, 100 VDCW; sim to Erie 8121-A100-U2J-1213.
C306	5491674P35	Tantalum: 120 pf $\pm$ 20%, 4 VDCW; sim to Sprague Type 162D.
C307	19A116192P10	Ceramic: 1500 pf $\pm$ 20%, 50 VDCW; sim to Erie 8121-050-WSR.
C308	19A116114P6059	Ceramic: 68 pf $\pm$ 5%, 100 VDCW; temp coef -470 PPM.
C309	5491674P28	Tantalum: 1.0 $\mu$ f $\pm$ 20%, 25 VDCW; sim to Sprague Type 162D.
C310	19A116192P1	Ceramic: 0.01 $\mu$ f $\pm$ 20%, 50 VDCW; sim to Erie 8121 SPECIAL.
C311 and C312	19A116114P13064	Ceramic: 100 pf $\pm$ 10%, 100 VDCW; temp coef -5600 PPM.
C313	19A116192P9	Ceramic: 820 pf $\pm$ 20%, 50 VDCW; sim to Erie 8111-050-WSR.
C314	5491674P28	Tantalum: 1.0 $\mu$ f $\pm$ 20%, 25 VDCW; sim to Sprague Type 162D.
C315	19A116080P104	Polyester: 0.033 $\mu$ f $\pm$ 10%, 50 VDCW.
C316	19A116244P2	Ceramic: 0.022 $\mu$ f $\pm$ 20%, 50 VDCW.
C317 and C318	19A116244P4	Ceramic: 0.15 $\mu$ f $\pm$ 20%, 50 VDCW.
C319	19A116114P7068	Ceramic: 120 pf $\pm$ 5%, 100 VDCW; temp coef -750 PPM.
C320	5496267P1	Tantalum: 6.8 $\mu$ f $\pm$ 20%, 6 VDCW; sim to Sprague Type 150D.
C321	5491674P30	Tantalum: 39 $\mu$ f $\pm$ 20%, 10 VDCW; sim to Sprague Type 162D.
C322	5491674P31	Tantalum: .033 $\mu$ f $\pm$ 20%, 35 VDCW; sim to Sprague Type 162D.
C323	5491674P30	Tantalum: 39 $\mu$ f $\pm$ 20%, 10 VDCW; sim to Sprague Type 162D.
C324	19A116192P13	Ceramic: 1000 pf $\pm$ 10%, 50 VDCW; sim to Erie 8121-A050-WSR.
C325	5491674P27	Tantalum: .47 $\mu$ f $\pm$ 20%, 35 VDCW; sim to Sprague Type 162D.
C326	5491674P28	Tantalum: 1.0 $\mu$ f $\pm$ 20%, 25 VDCW; sim to Sprague Type 162D.
C327	19A116244P4	Ceramic: 0.15 $\mu$ f $\pm$ 20%, 50 VDCW.
C328*	19A116244P5	Ceramic: 0.1 $\mu$ f $\pm$ 20%, 50 VDCW. Deleted by REV C.
C329	19A116178P7	Tantalum: 220 $\mu$ f $\pm$ 20%, 6 VDCW.
C330* thru C333*	19A116192P13	Ceramic: 1000 pf $\pm$ 10%, 50 VDCW; sim to Erie 8121-A050-WSR. Deleted by REV B.
C334	19A116192P13	Ceramic: 1000 pf $\pm$ 10%, 50 VDCW; sim to Erie 8121-A050-WSR.
C335*	19A116192P6	Ceramic: 0.022 $\mu$ f $\pm$ 20%, 50 VDCW; sim to Erie 8131-M050-WSR. Added by REV C.
CR301 thru CR303	19A115250P1	Diodes and Rectifiers - Silicon, fast recovery, 225 mA, 50 PIV.
FL302	19A134199P1	Filters - Bandpass: 20 KHz at 6 db, 40 KHz at 40 db.
FL303	19C304824G3	Bandpass: 23 MHz.
J301 and J302	19A116122P1	Jacks and Receptacles - Terminal, feed-thru.
L301	19A116308P3	Inductors - IF Transformer: sim to Toko, Inc. LMN-6586Y.

SYMBOL	GE PART NO.	DESCRIPTION
L302	19B219864G4 19B209436P1	Coil. Includes: Tuning slug.
L303	19A116308P1	IF Transformer: sim to Toko, Inc. LSN4816VE2.
L304	19A116308P2	IF Transformer: sim to Toko, Inc. LSN4817YV2.
P301 thru P304	19A115834P4	Plugs - Contact, electrical: sim to AMP 2-332070-9.
Q301	19A116223P1	Transistors - Silicon, PNP; sim to Type 2N3640.
Q302	19A116774P1	Silicon, NPN; sim to Type 2N5210.
Q303	19A115852P1	Silicon, PNP; sim to Type 2N3906.
Q304	19A115720P1	Silicon, NPN; sim to Type 2N2222.
Q305	19A115852P1	Silicon, PNP; sim to Type 2N3906.
Q306	19A134165P1	Silicon, PNP; sim to Type 2N2906A.
R301	3R151P470J	Resistors - Composition: 47 ohms $\pm$ 5%, 1/8 w.
R302	3R152P221J	Composition: 220 ohms $\pm$ 5%, 1/4 w.
R303	3R152P222J	Composition: 2.2K ohms $\pm$ 5%, 1/4 w.
R304	3R152P102J	Composition: 1K ohms $\pm$ 5%, 1/4 w.
R305	3R152P182J	Composition: 1.8K ohms $\pm$ 5%, 1/4 w.
R306	3R152P154J	Composition: 150K ohms $\pm$ 5%, 1/4 w.
R307	3R152P822J	Composition: 8.2K ohms $\pm$ 5%, 1/4 w.
R308	3R152P222J	Composition: 2.2K ohms $\pm$ 5%, 1/4 w.
R309	3R152P683J	Composition: 68K ohms $\pm$ 5%, 1/4 w.
R310	3R152P101J	Composition: 100 ohms $\pm$ 5%, 1/4 w.
R312	3R152P201J	Composition: 200 ohms $\pm$ 5%, 1/4 w.
R313	3R152P273J	Composition: 27K ohms $\pm$ 5%, 1/4 w.
R314	3R152P683J	Composition: 68K ohms $\pm$ 5%, 1/4 w.
R315	3R152P560J	Composition: 56 ohms $\pm$ 5%, 1/4 w.
R316	3R152P103J	Composition: 10K ohms $\pm$ 5%, 1/4 w.
R317	3R152P122J	Composition: 1.2K ohms $\pm$ 5%, 1/4 w.
R318 and R319	3R152P102J	Composition: 1K ohms $\pm$ 5%, 1/4 w.
R320	3R152P103J	Composition: 10K ohms $\pm$ 5%, 1/4 w.
R321	3R152P470J	Composition: 47 ohms $\pm$ 5%, 1/4 w.
R322	3R152P221J	Composition: 220 ohms $\pm$ 5%, 1/4 w.
R323	3R152P203J	Composition: 20K ohms $\pm$ 5%, 1/4 w.
R324	3R152P181J	Composition: 180 ohms $\pm$ 5%, 1/4 w.
R325	3R152P823J	Composition: 82K ohms $\pm$ 5%, 1/4 w.
R326	3R152P154J	Composition: 150K ohms $\pm$ 5%, 1/4 w.
R327*	3R151P103J	Composition: 10K ohms $\pm$ 5%, 1/8 w. Added by REV D.
U301	19C321359G1	Integrated Circuits - 2nd Oscillator, Mixer.
U302	19A116208P2	Monolithic, linear.
U303	19D423113G1	Detector.
U305	19C311995G4	Audio Amplifier. (Includes Tone Filter).
U306	19C311880G4	Squelch.
VR301	4036887P3	Voltage Regulators - Zener: 500 mW, 1.0 PIV.
Y302	19B206357G11	Crystals - Quartz: 23.455 MHz, temp range -30°C to +85°C.

SYMBOL	GE PART NO.	DESCRIPTION
	19A116477P1	Miscellaneous - Machine screw: 5/32. (Secures A307).
	19B216316P1	Insulator. (Used with J301, J302).
	19A116120P1	Can. (Used with L302).
	19B226696P1	Shield. (Located at L303, L304).
	19B219802P2	Shield. (Located over A10 and L16-L20).
	19B200497P5	Tuning slug. (Used with Multiplier).
		Associated Assemblies Connector Kit 19C321535G1
C1	19A116114P1	Capacitors - Ceramic: 1 pf $\pm$ 10%, 100 VDCW; temp coef 0 PPM. (Part of W1).
C2	19A116114P1	Ceramic: 1 $\mu$ f $\pm$ 10%, 100 VDCW; temp coef 0 PPM.
J1	7776570P17	Jacks and Receptacles - Receptacle, bulkhead: coaxial, 500 v peak. Military Type KS35179 REV.B-1094/U.
W1	19B226852G1	Cables - Cable assembly. Includes C1.

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

REV A & B - Receiver Front End 19C317295G6 Incorporated in initial shipment.

REV C - To improve ease in assembly, troubleshooting and repairing. Changed RF Amp/Mixer.

REV A - Receiver Board 19D423091G3 & G4 To improve attack time with Channel Guard Option. Relocated C325.

REV B - To improve reliability. Deleted C330 through C333.

REV C - To eliminate manufacture of non-Channel Guard receiver boards. Deleted from Schematic Diagram call out of U304, C328, 1r1 and circle (●) in front of C335. Deleted Note: ● Used for Channel Guard receivers.

REV. D -To improve stability. Added R327.

QUICK CHECKS

SYMPTOM	PROCEDURE
No Audio	<ol style="list-style-type: none"><li>1. Check audio waveform at the top of the Volume Control (see Step 2).</li><li>2. If audio is present, check voltage readings of Audio and Squelch modules (see Schematic Diagram).</li><li>3. If audio is not present, check gain and current readings of Front End and IF modules (see Steps 1 &amp; 3).</li></ol>
Poor Sensitivity	<ol style="list-style-type: none"><li>1. Measure the gain of the Mixer stage (see Step 3). If low, measure the gain of the RF amplifier and of Squelch module (see Step 2).</li></ol>
Improper Squelch Operation	<ol style="list-style-type: none"><li>1. Check the noise waveform at the input to the Squelch module and at Squelch Control high (see Step 2).</li><li>2. Measure the DC voltages for the Squelch module (squelched and unsquelched).</li></ol>

